

<b>Notice of References Cited</b>	Application/Control No. 10/749,500	Applicant(s)/Patent Under Reexamination WINDLASS ET AL.	
	Examiner Mai-Huong Tran	Art Unit 2818	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,812,509	11-2004	Xu, Baomin	257/295
	B	US-6,878,980	04-2005	Gudesen et al.	257/295
	C	US-6,582,569	06-2003	Chiang et al.	204/192.17
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ljungcrantz et al., Method for Making a Ferroelectric Memory Cell in a Ferroelectric Memory Device, and a Ferroelectric Memory Device, Pub. date Oct. 21, 2004, Pub. No. US 2004/0209420.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.